

AF/GAU 2822



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH
Docket No.: 303.229US2 Serial No.: 09/132,157
Filed: August 11, 1998 Due Date: January 30, 2001
Examiner: Mark V. Prenty Group Art Unit: 2822

Box AF

Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

- A return postcard.
 An Amendment and Response After Final (7 Pages).

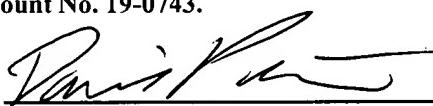
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Box AF, Commissioner for Patents, Washington, D.C. 20231, on this 22 day of December, 2000.

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(GENERAL)



EXPEDITED PROCEDURE - EXAMINING GROUP 2822

S/N 09/132,157

PATENT

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AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

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In response to the Final Office Action mailed October 30, 2000, please amend the application as follows.

IN THE CLAIMS

Please cancel claims 30-31 without prejudice or disclaimer. Please amend claims 11, 24, 25, 28, 32, 38-41, and 43 as follows. Claims 11, 13-14, 24-28, 32, 38-43 are now pending in the application.

11. (Five times amended) A p-channel metal-oxide-semiconductor transistor, comprising:
a silicon substrate;
a silicon dioxide (SiO_2) gate oxide, coupled to the substrate;
a gate, coupled to the SiO_2 gate oxide;
source/drain regions formed in the substrate on opposite sides of the gate; and
a $\text{Si}_{1-x}\text{Ge}_x$ channel region, having a germanium molar fraction x, located
underneath [and formed in the substrate, underneath and adjoining] the SiO_2 gate oxide
and between the source/drain regions[;], wherein x is less than or equal to 0.6, and
wherein the $\text{Si}_{1-x}\text{Ge}_x$ channel region forms a $\text{Si}_{1-x}\text{Ge}_x/\text{SiO}_2$ gate oxide interface.
[wherein the $\text{Si}_{1-x}\text{Ge}_x$ channel region has a channel length less than 7 μm .]

24. (Five times amended) A p-channel metal-oxide-semiconductor transistor formed on a silicon substrate, comprising: